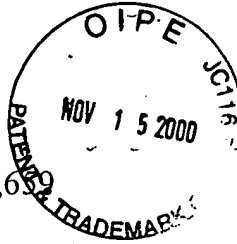


GP 2814
#6/d
11-18-00
SEC. 636
109/313,659

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Won-suk YANG et al.



Group Art Unit: 2814

Application Serial No.: 09/313,659

Examiner: S. Rao

Filed: May 18, 1999

Title: METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE

Assistant Commissioner of Patents
Washington, D.C. 20231

RESPONSE TO OFFICE ACTION

RECEIVED
NOV 17 2000
TECHNOLOGY CENTER 2800

Sir:

In response to the Office Action dated August 15, 2000, the period for response to which extends through November 15, 2000, please consider the following amendments.

IN THE TITLE:

Please cancel the current title and replace it with the following.

--METHOD OF FABRICATING A MOS TRANSISTOR WITH DOUBLE
SIDEWALL SPACERS IN A PERIPHERAL REGION AND SINGLE SIDEWALL
SPACERS IN A CELL REGION--.

IN THE SPECIFICATION:

Please amend the specification as follows.

a